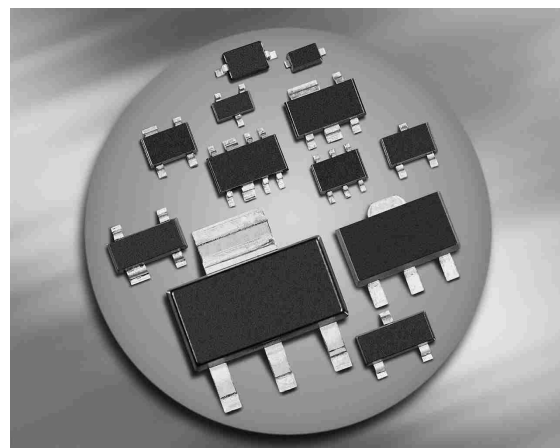


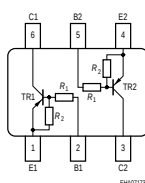
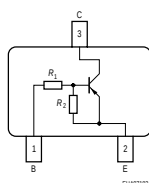
PNP Silicon Digital Transistor

- Switching circuit, inverter, interface circuit, driver circuit
- Built in bias resistor ($R_1 = 47\text{ k}\Omega$, $R_2 = 47\text{ k}\Omega$)
- BCR198S: Two internally isolated transistors with good matching in one multichip package
- BCR198S: For orientation in reel see package information below
- Pb-free (RoHS compliant) package ¹⁾
- Qualified according AEC Q101



BCR198/F BCR198W

BCR198S



Type	Marking	Pin Configuration						Package
BCR198	WRs	1=B	2=E	3=C	-	-	-	SOT23
BCR198F	WRs	1=B	2=E	3=C	-	-	-	TSFP-3
BCR198S	WRs	1=E1	2=B1	3=C2	4=E2	5=B2	6=C1	SOT363
BCR198W	WRs	1=B	2=E	3=C	-	-	-	SOT323

¹Pb-containing package may be available upon special request

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}	50	V
Collector-base voltage	V_{CBO}	50	
Input forward voltage	$V_{i(fwd)}$	80	
Input reverse voltage	$V_{i(rev)}$	10	
Collector current	I_C	100	mA
Total power dissipation- BCR198, $T_S \leq 102^\circ\text{C}$ BCR198F, $T_S \leq 128^\circ\text{C}$ BCR198S, $T_S \leq 115^\circ\text{C}$ BCR198W, $T_S \leq 124^\circ\text{C}$	P_{tot}	200 250 250 250	mW
Junction temperature	T_j	150	
Storage temperature	T_{stg}	-65 ... 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾	R_{thJS}		K/W
BCR198		≤ 240	
BCR198F		≤ 90	
BCR198S		≤ 140	
BCR198W		≤ 105	

¹⁾For calculation of R_{thJA} please refer to Application Note Thermal Resistance

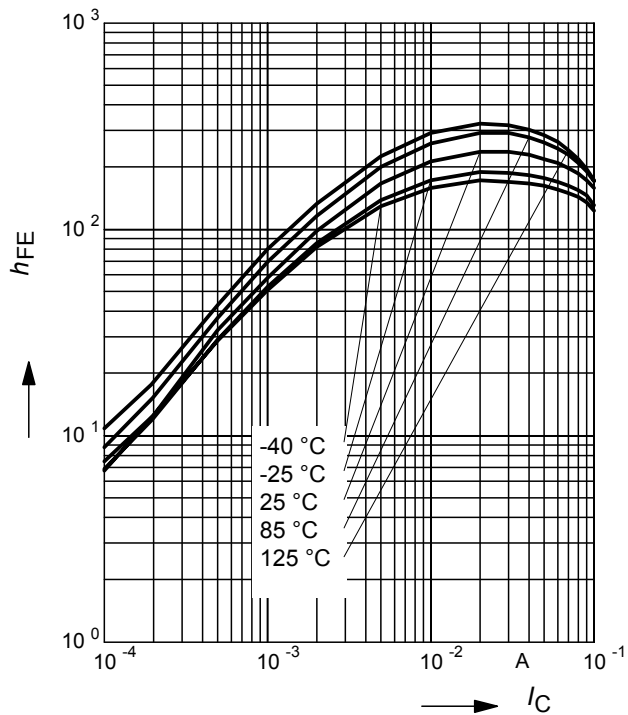
Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage $I_C = 100\ \mu\text{A}$, $I_B = 0$	$V_{(\text{BR})\text{CEO}}$	50	-	-	V
Collector-base breakdown voltage $I_C = 10\ \mu\text{A}$, $I_E = 0$	$V_{(\text{BR})\text{CBO}}$	50	-	-	
Collector-base cutoff current $V_{\text{CB}} = 40\ \text{V}$, $I_E = 0$	I_{CBO}	-	-	100	nA
Emitter-base cutoff current $V_{\text{EB}} = 10\ \text{V}$, $I_C = 0$	I_{EBO}	-	-	164	μA
DC current gain ¹⁾ $I_C = 5\ \text{mA}$, $V_{\text{CE}} = 5\ \text{V}$	h_{FE}	70	-	-	-
Collector-emitter saturation voltage ¹⁾ $I_C = 10\ \text{mA}$, $I_B = 0.5\ \text{mA}$	V_{CEsat}	-	-	0.3	V
Input off voltage $I_C = 100\ \mu\text{A}$, $V_{\text{CE}} = 5\ \text{V}$	$V_{\text{i(off)}}$	0.8	-	1.5	
Input on voltage $I_C = 2\ \text{mA}$, $V_{\text{CE}} = 0.3\ \text{V}$	$V_{\text{i(on)}}$	1	-	3	
Input resistor	R_1	32	47	62	k Ω
Resistor ratio	R_1/R_2	0.9	1	1.1	-
AC Characteristics					
Transition frequency $I_C = 10\ \text{mA}$, $V_{\text{CE}} = 5\ \text{V}$, $f = 100\ \text{MHz}$	f_{T}	-	190	-	MHz
Collector-base capacitance $V_{\text{CB}} = 10\ \text{V}$, $f = 1\ \text{MHz}$	C_{cb}	-	3	-	pF

¹⁾Pulse test: $t < 300\ \mu\text{s}$; $D < 2\%$

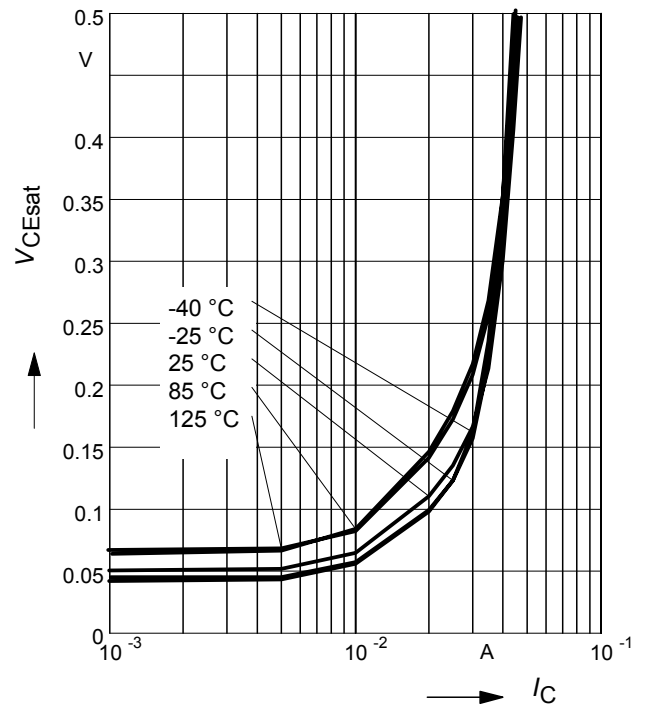
DC current gain $h_{FE} = f(I_C)$

$V_{CE} = 5 \text{ V}$ (common emitter configuration)



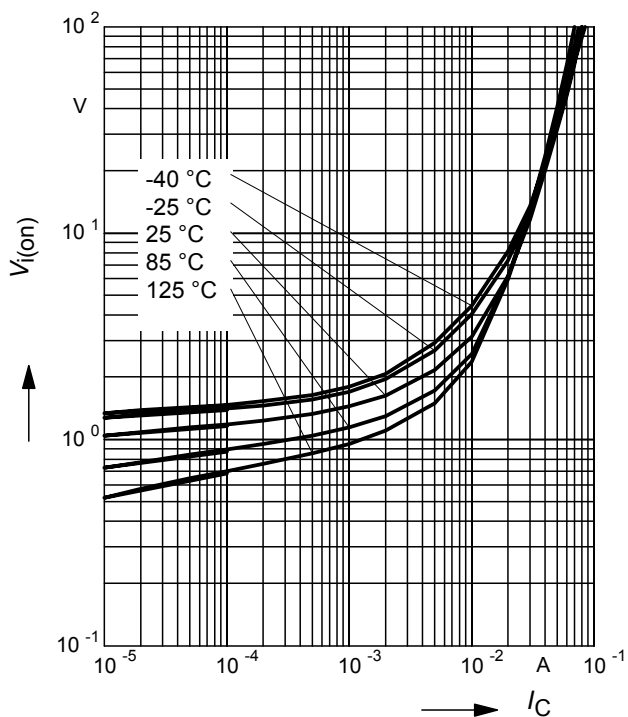
Collector-emitter saturation voltage

$V_{CEsat} = f(I_C), h_{FE} = 20$



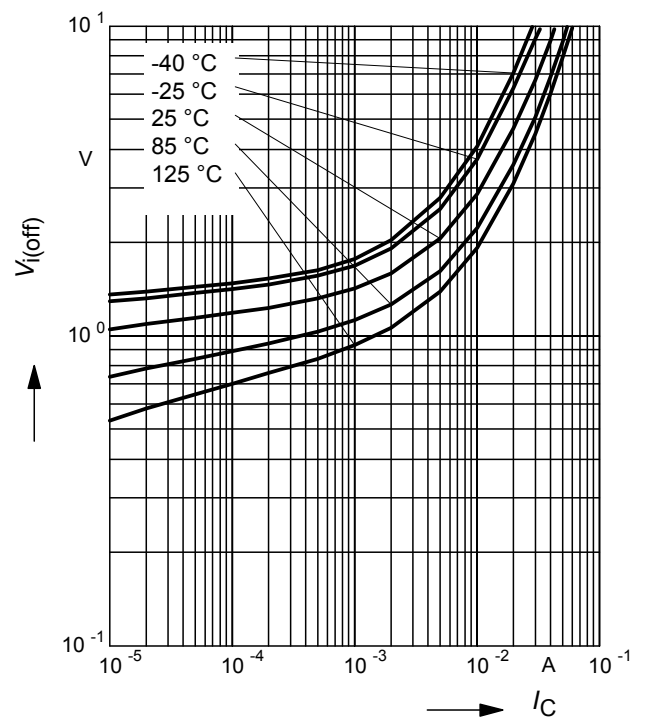
Input on Voltage $V_{i(on)} = f(I_C)$

$V_{CE} = 0.3 \text{ V}$ (common emitter configuration)



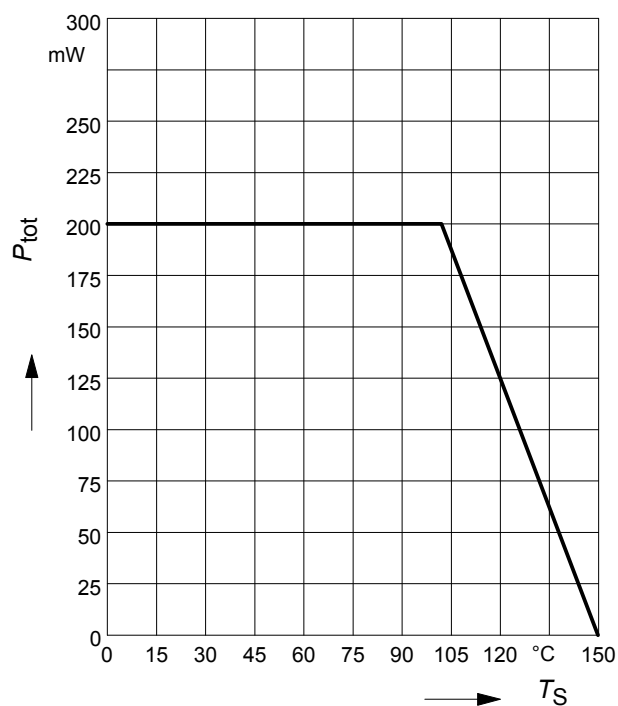
Input off voltage $V_{i(off)} = f(I_C)$

$V_{CE} = 5 \text{ V}$ (common emitter configuration)



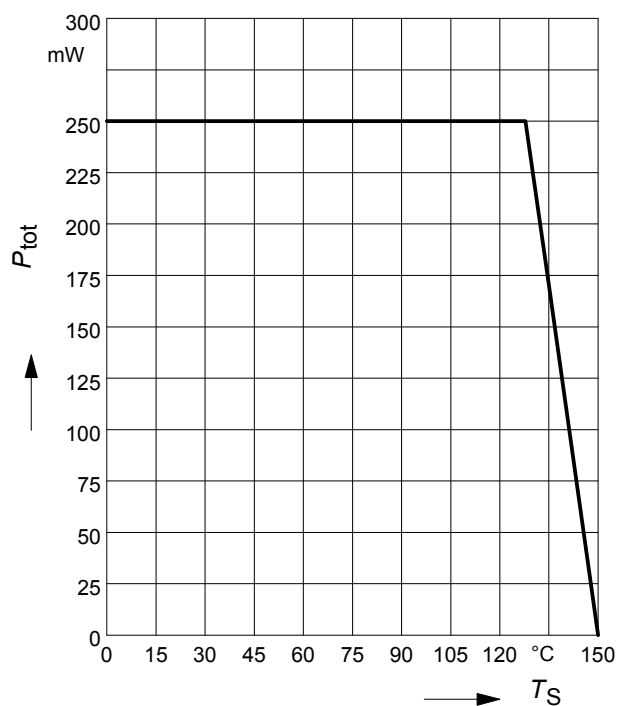
Total power dissipation $P_{\text{tot}} = f(T_S)$

BCR198



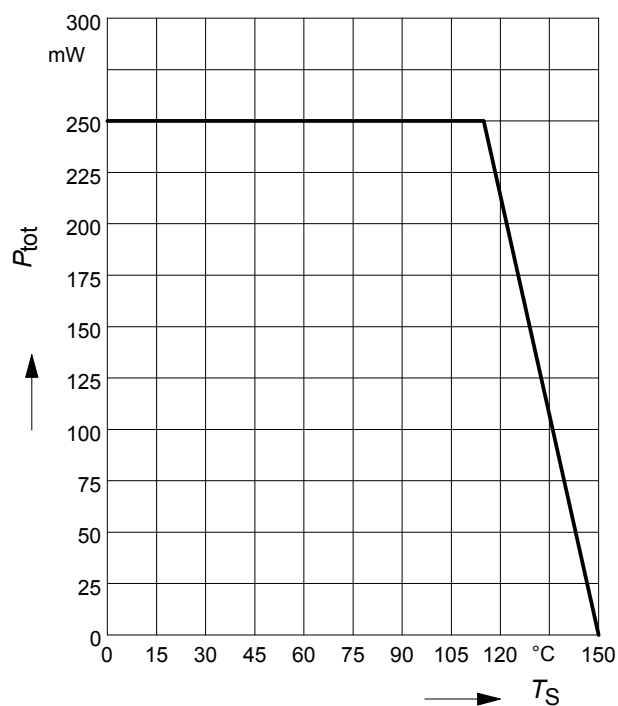
Total power dissipation $P_{\text{tot}} = f(T_S)$

BCR198F



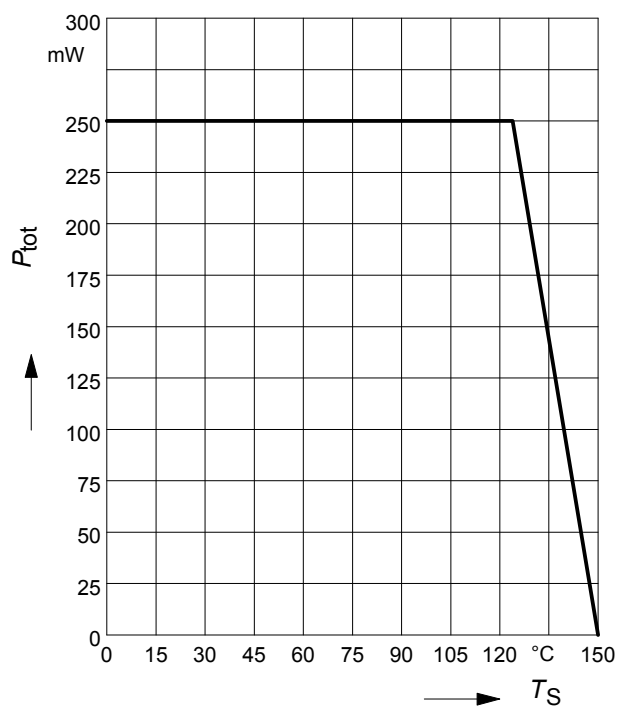
Total power dissipation $P_{\text{tot}} = f(T_S)$

BCR198S



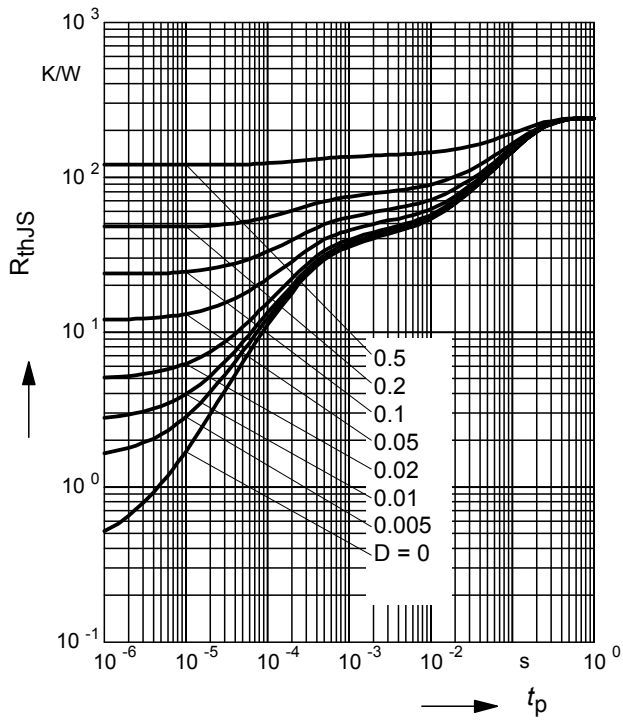
Total power dissipation $P_{\text{tot}} = f(T_S)$

BCR198W



Permissible Pulse Load $R_{thJS} = f(t_p)$

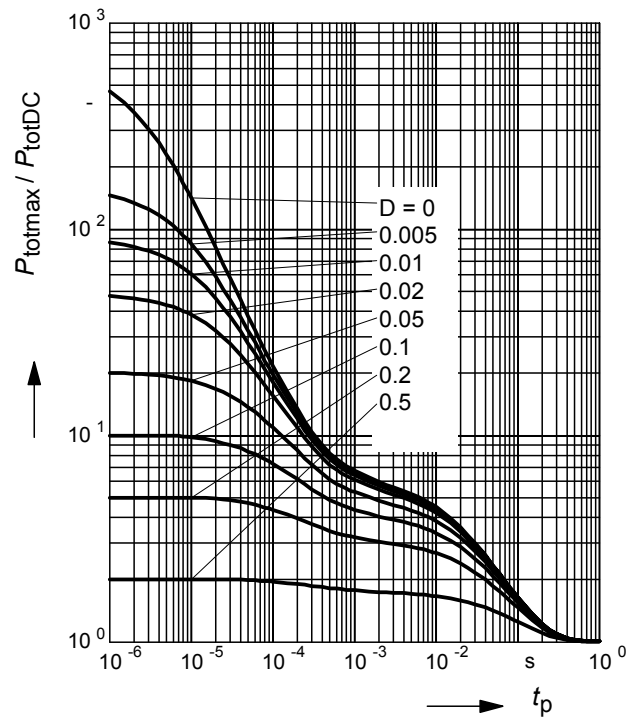
BCR198



Permissible Pulse Load

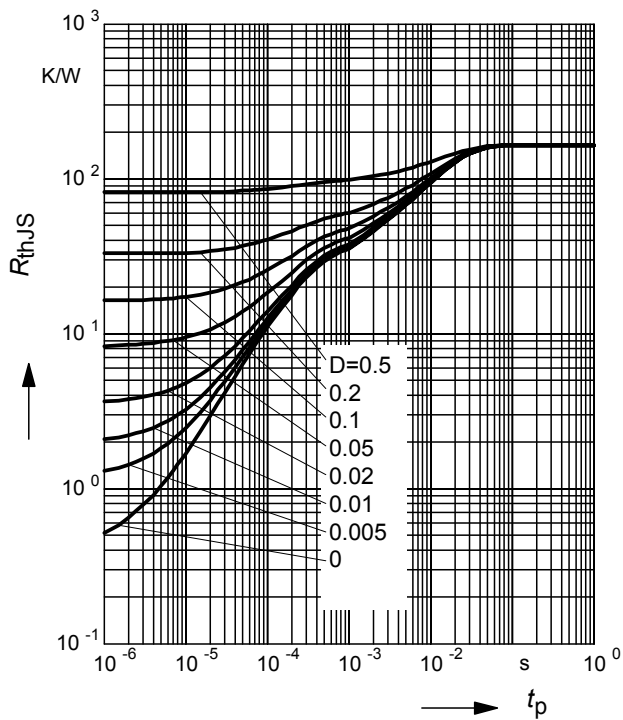
$$P_{totmax}/P_{totDC} = f(t_p)$$

BCR198



Permissible Puls Load $R_{thJS} = f(t_p)$

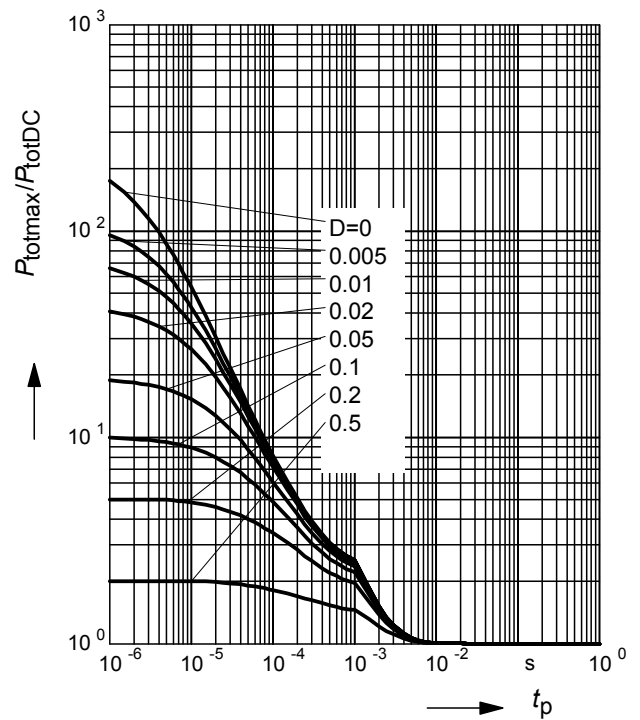
BCR198F



Permissible Pulse Load

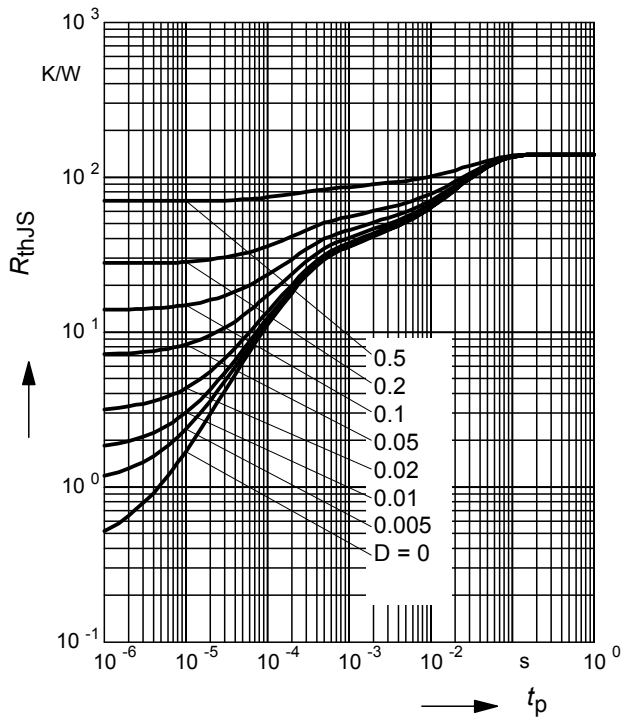
$$P_{totmax}/P_{totDC} = f(t_p)$$

BCR198F



Permissible Puls Load $R_{thJS} = f(t_p)$

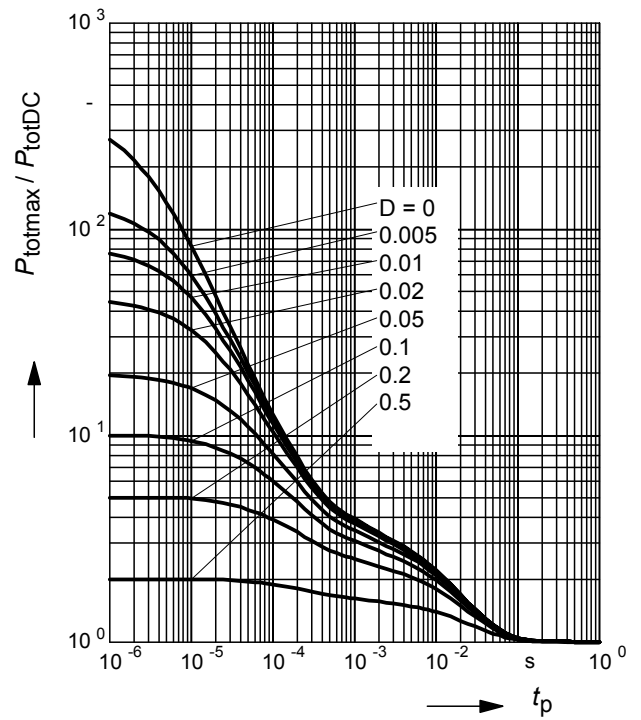
BCR198S



Permissible Pulse Load

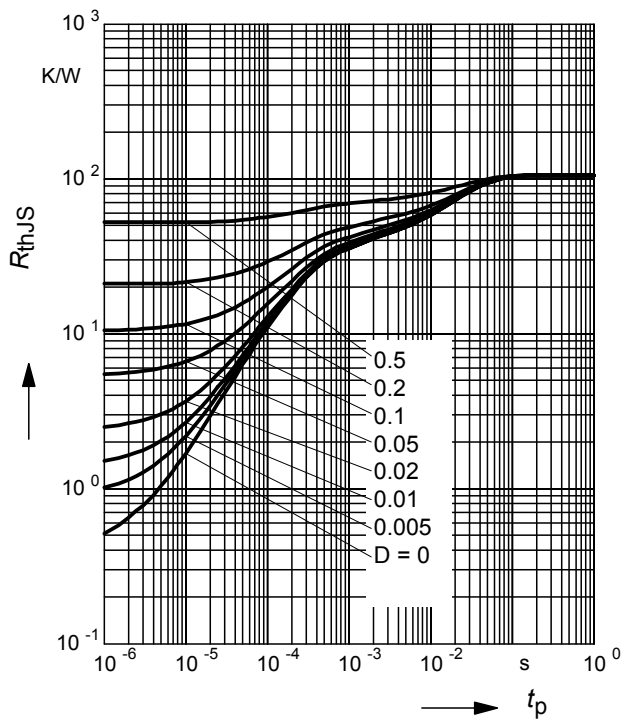
$$P_{totmax}/P_{totDC} = f(t_p)$$

BCR198S



Permissible Puls Load $R_{thJS} = f(t_p)$

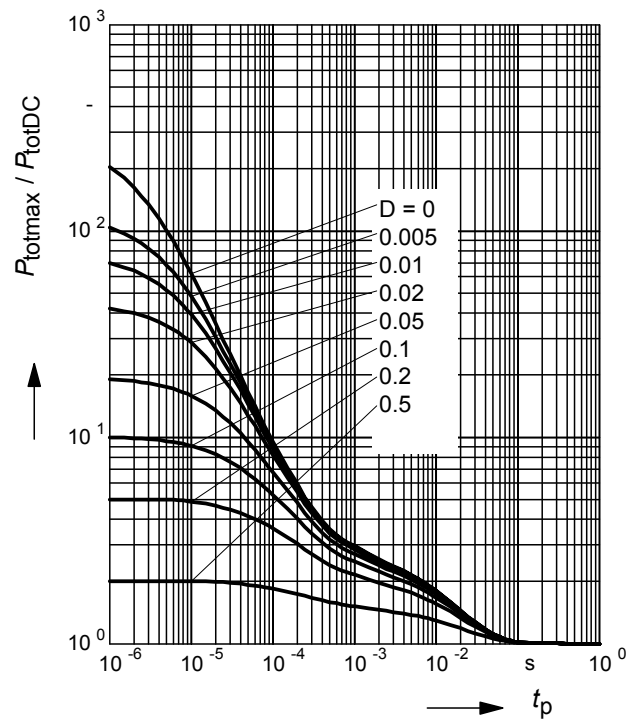
BCR198W

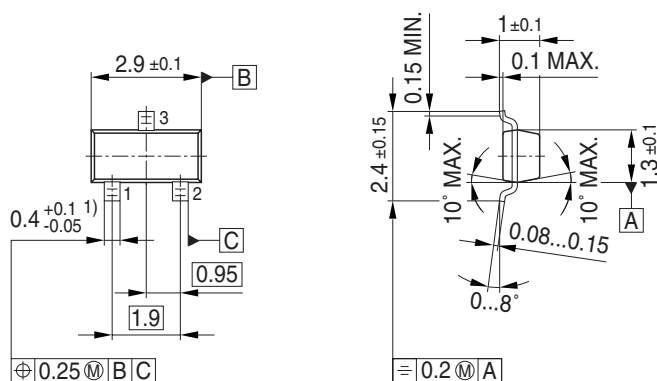


Permissible Pulse Load

$$P_{totmax}/P_{totDC} = f(t_p)$$

BCR198W





Foot Print

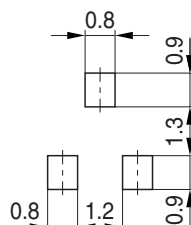
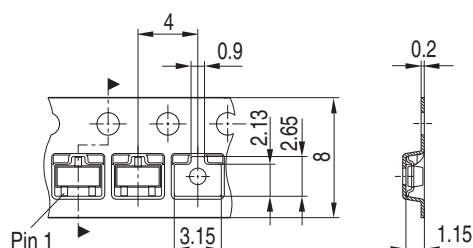


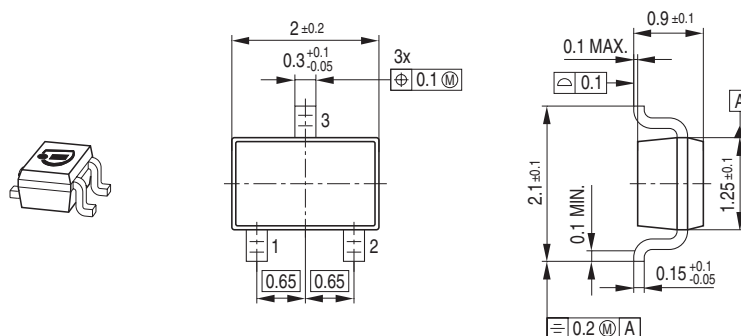
Diagram illustrating the marking on the BCW66 component:

- Manufacturer:** infineon
- Date code (YM):** 2005, June (represented by 6 and 5)
- Type code:** BCW66
- Pin 1:** Indicated by a line pointing to the first pin.

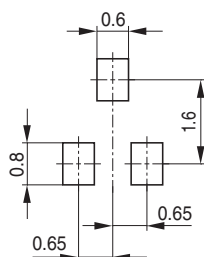
Reel ø180 mm = 3.000 Pieces/Reel
Reel ø330 mm = 10.000 Pieces/Reel



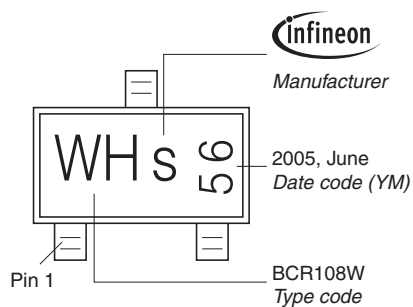
Package Outline



Foot Print

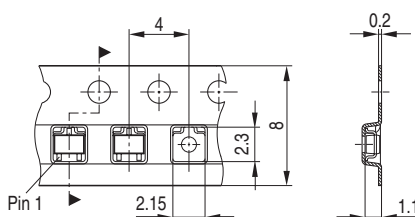


Marking Layout (Example)

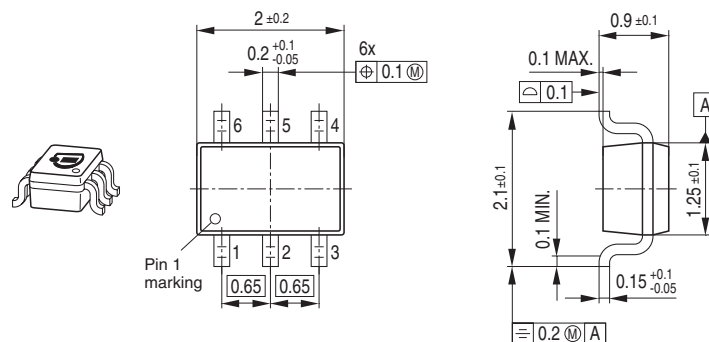


Standard Packing

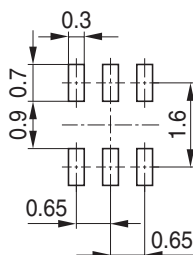
Reel $\varnothing 180 \text{ mm}$ = 3.000 Pieces/Reel
 Reel $\varnothing 330 \text{ mm}$ = 10.000 Pieces/Reel



Package Outline

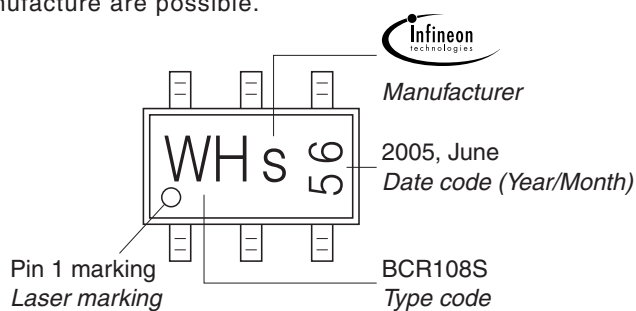


Foot Print



Marking Layout (Example)

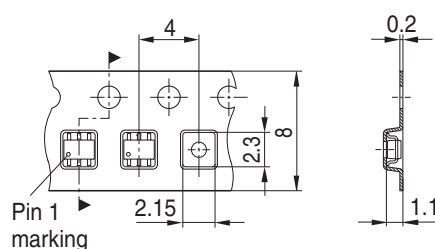
Small variations in positioning of Date code, Type code and Manufacture are possible.



Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel
Reel ø330 mm = 10.000 Pieces/Reel

For symmetric types no defined Pin 1 orientation in reel.



[illegible]

Technical drawing of a mechanical part. The drawing shows a top view and a side view. The top view is a rectangle with a width of 0.4 and a height of 0.45. The side view is a rectangle with a width of 0.4 and a height of 1.05. The drawing is labeled with dimensions: 0.4, 0.45, 1.05, and 0.4.

Diagram illustrating the marking on the BCR847BF diode:

- Manufacturer:** infineon
- Pin 1:** Indicated by a line pointing to the first pin.
- Type code:** BCR847BF

Technical drawing of a mechanical part showing a top view and a side view. The top view includes dimensions: 4, 0.3, 1.2, 1.5, 8, 1.35, and Pin 1. The side view includes dimensions: 0.2 and 0.7.

Edition 2006-02-01

Published by

Infineon Technologies AG

81726 München, Germany

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